ESE 3190 Lab 3: PLUOS Vov= Vas-V+4 ganalor linear GOH OB *although the polarities

R are opposite that (Incle) / saturation of nelos, people e usually graph the TMOS IV characteristics Le same as nMOS using absolute value VDS/ TMOS equations: Iriode region: IVDS/ < |VGS-VALI) 10 = Kp L [(V65 - V7H) VD5 - = VPS] saturation region: Nos1 > Nos- Vanl 10 = = { K' W (Nes-VIH) 2 -> taking into account : 10 = 2 kp 2 (Vos-V+H)? (1+ IVs) drained width modulation $V_{m} = -0.73V$ a) $V_{DS} = -V_{S}$ $V_{m} = -0.73V$ a) $V_{DS} = -V_{S}$ $V_{S} = -V_{S}$ Vre-Lab: D) VS=OV: 10=0 since VGS=0>V+H Vs = N: 10 = - 29 m4 (-1V+0.73V) = -0.100m4 V5=COV: 10= Z md ((N+073)) Ng =1 20 1 / 0= - 29 mt (-2V+0.73V)2=-2.34 mA 510 = -40.3mA Vs = 3V: 1p = - 29 m/2 (-3V + 0.73V)2 = -7,47 mA Vg = 4V: in = - 29 m/2 (-4V+0.73V)2 = - 15,5 m/2 * plot on separate
page Vs=5V: in=-29 mf (-5V+0-73V)2-- 2Ce. 44 mA

$$V_{0} = \frac{1}{1} V_{0} V_{0} = \frac{1}{1} V_{0$$